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### Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

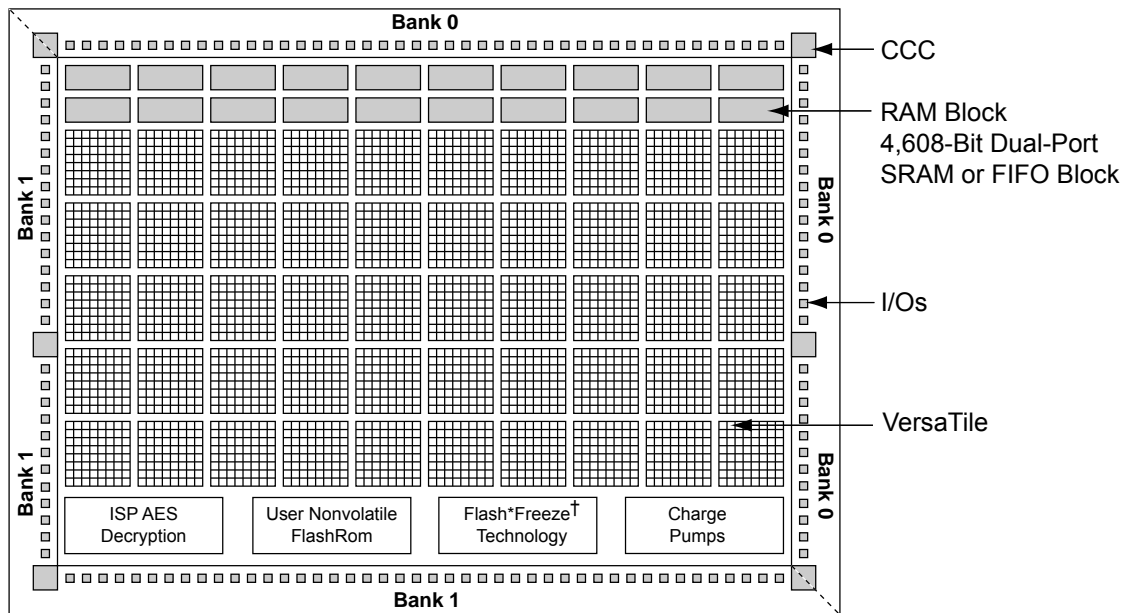
Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

### Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

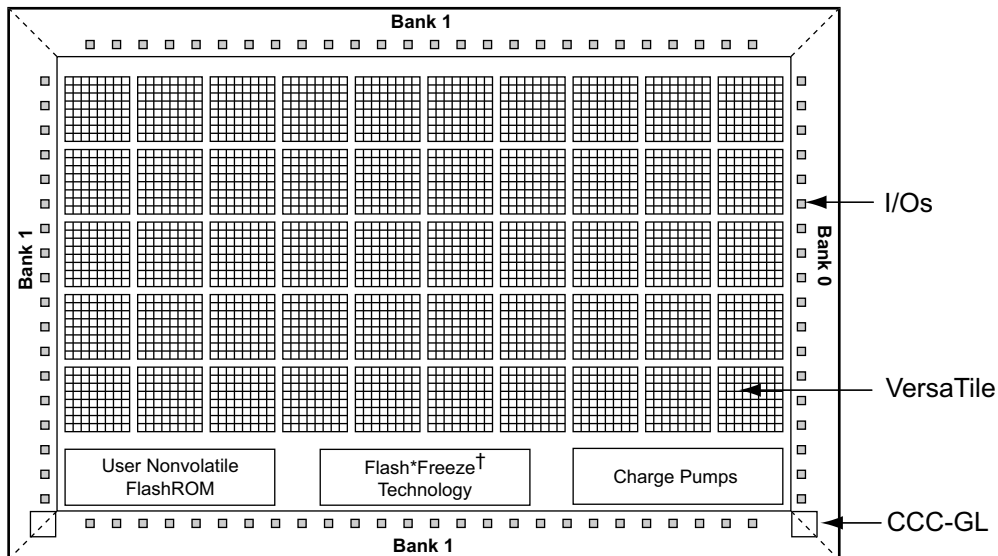
#### Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	147456
Number of I/O	177
Number of Gates	1000000
Voltage - Supply	1.14V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	256-LBGA
Supplier Device Package	256-FPBGA (17x17)
Purchase URL	<a href="https://www.e-xfl.com/product-detail/microchip-technology/m1a3p1000l-1fg256">https://www.e-xfl.com/product-detail/microchip-technology/m1a3p1000l-1fg256</a>



Note: † Flash\*Freeze mode is supported on IGL00 devices.

**Figure 1-3 • IGLOO Device Architecture Overview with Two I/O Banks with RAM and PLL (60 k and 125 k gate densities)**



Note: † Flash\*Freeze mode is supported on IGL00 devices.

**Figure 1-4 • IGLOO Device Architecture Overview with Three I/O Banks (AGLN015, AGLN020, A3PN015, and A3PN020)**

- There will be added skew and clock insertion delay due to the clock gating circuit. The user should analyze external setup/hold times carefully. The user should also ensure the additional skew across the clock gating filter circuit is accounted for in any paths where the launch register is driven from the filter input clock and captured by a register driven by the gated clock filter output clock.

## Power Analysis

SmartPower identifies static and dynamic power consumption problems quickly within a design. It provides a hierarchical view, allowing users to drill down and estimate the power consumption of individual components or events. SmartPower analyzes power consumption for nets, gates, I/Os, memories, clocks, cores, clock domains, power supply rails, peak power during a clock cycle, and switching transitions.

SmartPower generates detailed hierarchical reports of the dynamic power consumption of a design for easy inspection. These reports include design-level power summary, average switching activity, and ambient and junction temperature readings. Enter the target clock and data frequencies for a design, and let SmartPower perform a detailed and accurate power analysis. SmartPower supports importing files in the VCD (Value-Change Dump) format as specified in the IEEE 1364 standard. It also supports the Synopsys® Switching Activity Interchange Format (SAIF) standard. Support for these formats lets designers generate switching activity information in a variety of simulators and then import this information directly into SmartPower.

For portable or battery-operated applications, a power profile feature enables you to measure power and battery life, based on a sequence of operational modes of the design. In most portable and battery-operated applications, the system is seldom fully "on" 100 percent of the time. "On" is a combination of fully active, standby, sleep, or other functional modes. SmartPower allows users to create a power profile for a design by specifying operational modes and the percent of time the device will run in each of the modes. Power is calculated for each of the modes, and total power is calculated based on the weighted average of all modes.

SmartPower also provides an estimated battery life based on the power profile. The current capacity for a given battery is entered and used to estimate the life of the battery. The result is an accurate and realistic indication of battery life.

More information on SmartPower can be found on the Microsemi SoC Products Group website:  
<http://www.microsemi.com/soc/products/software/libero/smartpower.aspx>.

## Additional Power Conservation Techniques

IGLOO, IGLOO nano, IGLOO PLUS, ProASIC3L, and RT ProASIC3 FPGAs provide many ways to inherently conserve power; however, there are also several design techniques that can be used to reduce power on the board.

- Microsemi recommends that the designer use the minimum number of I/O banks possible and tie any unused power supplies (such as  $V_{CCPLL}$ ,  $V_{CCI}$ ,  $V_{MV}$ , and  $V_{PUMP}$ ) to ground.
- Leave unused I/O ports floating. Unused I/Os are configured by the software as follows:
  - Output buffer is disabled (with tristate value of high impedance)
  - Input buffer is disabled (with tristate value of high impedance)
- Use the lowest available voltage I/O standard, the lowest drive strength, and the slowest slew rate to reduce I/O switching contribution to power consumption.
- Advanced and pro I/O banks may consume slightly higher static current than standard and standard plus banks—avoid using advanced and pro banks whenever practical.
  - The small static power benefit obtained by avoiding advanced or pro I/O banks is usually negligible compared to the benefit of using a low power I/O standard.
- Deselect RAM blocks that are not being used.
- Only enable read and write ports on RAM blocks when they are needed.
- Gating clocks LOW offers improved static power of RAM blocks.
- Drive the FF port of RAM blocks with the Flash\_Freeze\_Enabled signal from the Flash\*Freeze management IP.
- Drive inputs to the full voltage level so that all transistors are turned on or off completely.

**Table 3-3 • Quadrant Global Pin Name (continued)**

Differential I/O Pairs	GAAO/IOuxwByVz GAA1/IOuxwByVz	The output of the different pair will drive the global.
	GABO/IOuxwByVz GAB1/IOuxwByVz	The output of the different pair will drive the global.
	GACO/IOuxwByVz GAC1/IOuxwByVz	The output of the different pair will drive the global.
	GBAO/IOuxwByVz GBA1/IOuxwByVz	The output of the different pair will drive the global.
	GBBO/IOuxwByVz GBB1/IOuxwByVz	The output of the different pair will drive the global.
	GBCO/IOuxwByVz GBC1/IOuxwByVz	The output of the different pair will drive the global.
	GDAO/IOuxwByVz GDA1/IOuxwByVz	The output of the different pair will drive the global.
	GDBO/IOuxwByVz GDB1/IOuxwByVz	The output of the different pair will drive the global.
	GDCO/IOuxwByVz GDC1/IOuxwByVz	The output of the different pair will drive the global.
	GEAO/IOuxwByVz GEA1/IOuxwByVz	The output of the different pair will drive the global.
	GEBO/IOuxwByVz GEB1/IOuxwByVz	The output of the different pair will drive the global.
	GECO/IOuxwByVz GEC1/IOuxwByVz	The output of the different pair will drive the global.

*Note: Only one of the I/Os can be directly connected to a quadrant at a time.*

## Unused Global I/O Configuration

The unused clock inputs behave similarly to the unused Pro I/Os. The Microsemi Designer software automatically configures the unused global pins as inputs with pull-up resistors if they are not used as regular I/O.

## I/O Banks and Global I/O Standards

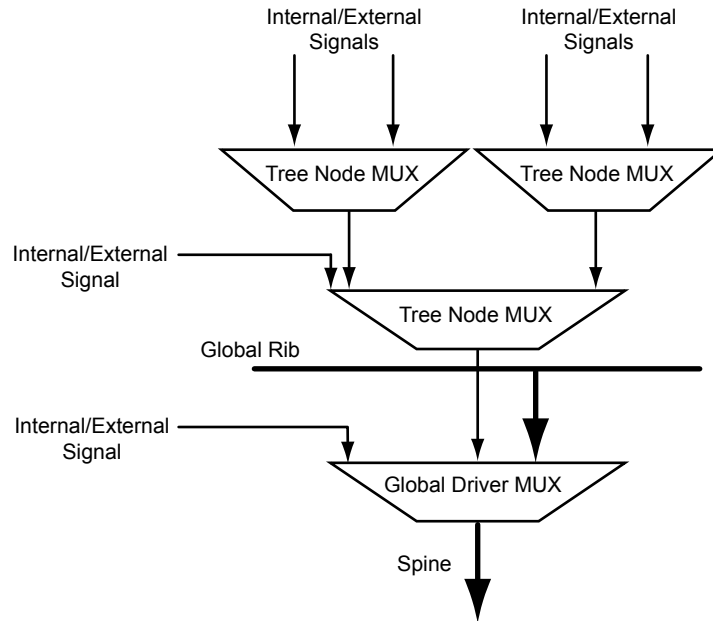
In low power flash devices, any I/O or internal logic can be used to drive the global network. However, only the global macro placed at the global pins will use the hardwired connection between the I/O and global network. Global signal (signal driving a global macro) assignment to I/O banks is no different from regular I/O assignment to I/O banks with the exception that you are limited to the pin placement location available. Only global signals compatible with both the VCCI and VREF standards can be assigned to the same bank.



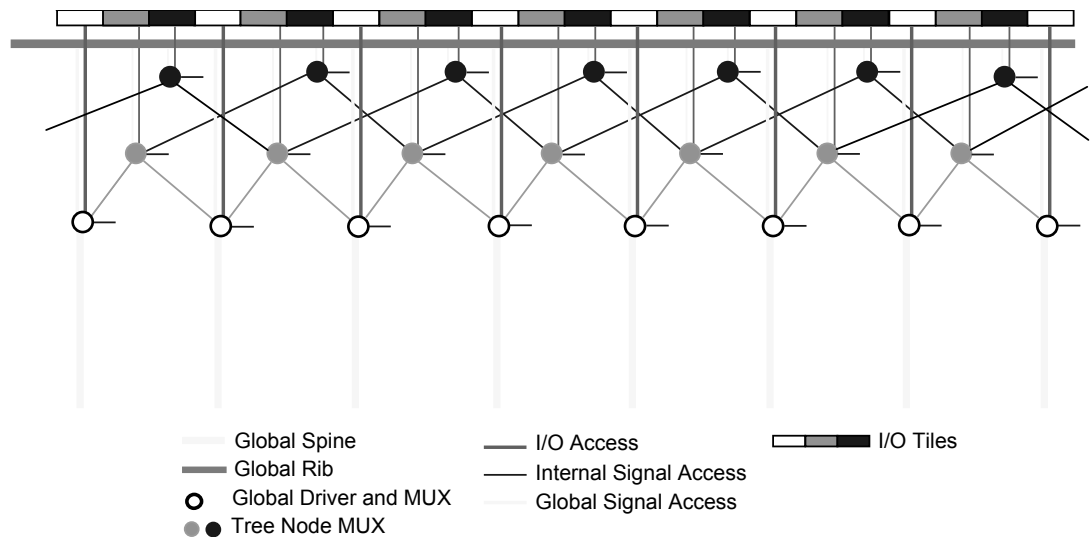
## Using Clock Aggregation

Clock aggregation allows for multi-spine clock domains to be assigned using hardwired connections, without adding any extra skew. A MUX tree, shown in Figure 3-8, provides the necessary flexibility to allow long lines, local resources, or I/Os to access domains of one, two, or four global spines. Signal access to the clock aggregation system is achieved through long-line resources in the central rib in the center of the die, and also through local resources in the north and south ribs, allowing I/Os to feed directly into the clock system. As Figure 3-9 indicates, this access system is contiguous.

There is no break in the middle of the chip for the north and south I/O VersaNet access. This is different from the quadrant clocks located in these ribs, which only reach the middle of the rib.



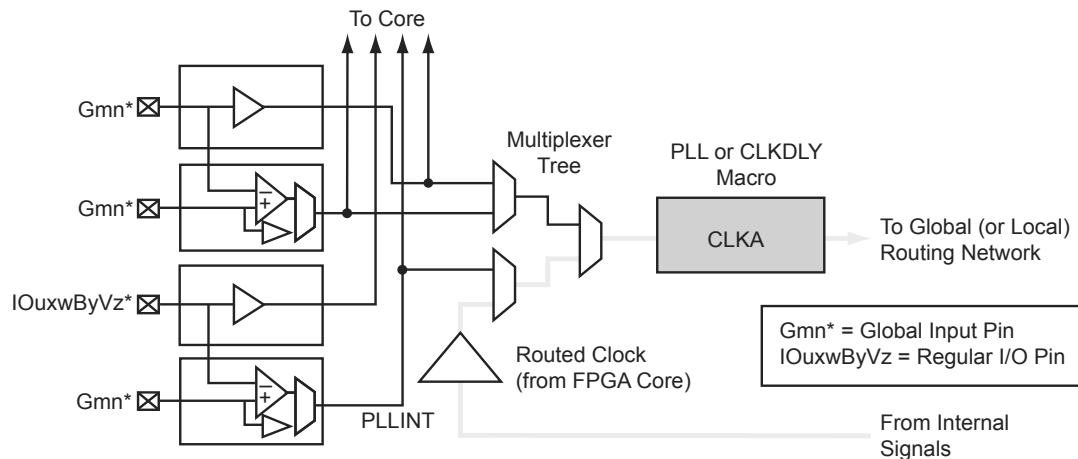
**Figure 3-8 • Spine Selection MUX of Global Tree**



**Figure 3-9 • Clock Aggregation Tree Architecture**

## Core Logic Clock Source

Core logic refers to internal routed nets. Internal routed signals access the CCC via the FPGA Core Fabric. Similar to the External I/O option, whenever the clock source comes internally from the core itself, the routed signal is instantiated with a PLLINT macro before connecting to the CCC clock input (see Figure 4-12 for an example illustration of the connections, shown in red).



**Figure 4-12 • Illustration of Core Logic Usage**

For Fusion devices, the input reference clock can also be from the embedded RC oscillator and crystal oscillator. In this case, the CCC configuration is the same as the hardwired I/O clock source, and users are required to instantiate the RC oscillator or crystal oscillator macro and connect its output to the input reference clock of the CCC block.

global assignments are not allocated properly. See the "Physical Constraints for Quadrant Clocks" section for information on assigning global signals to the quadrant clock networks.

Promoted global signals will be instantiated with CLKINT macros to drive these signals onto the global network. This is automatically done by Designer when the Auto-Promotion option is selected. If the user wishes to assign the signals to the quadrant globals instead of the default chip globals, this can be done by using ChipPlanner, by declaring a physical design constraint (PDC), or by importing a PDC file.

### **Physical Constraints for Quadrant Clocks**

If it is necessary to promote global clocks (CLKBUF, CLKINT, PLL, CLKDLY) to quadrant clocks, the user can define PDCs to execute the promotion. PDCs can be created using PDC commands (pre-compile) or the MultiView Navigator (MVN) interface (post-compile). The advantage of using the PDC flow over the MVN flow is that the Compile stage is able to automatically promote any regular net to a global net before assigning it to a quadrant. There are three options to place a quadrant clock using PDC commands:

- Place a clock core (not hardwired to an I/O) into a quadrant clock location.
- Place a clock core (hardwired to an I/O) into an I/O location (set\_io) or an I/O module location (set\_location) that drives a quadrant clock location.
- Assign a net driven by a regular net or a clock net to a quadrant clock using the following command:

```
assign_local_clock -net <net name> -type quadrant <quadrant clock region>
```

where

<net name> is the name of the net assigned to the local user clock region.

<quadrant clock region> defines which quadrant the net should be assigned to. Quadrant clock regions are defined as UL (upper left), UR (upper right), LL (lower left), and LR (lower right).

Note: If the net is a regular net, the software inserts a CLKINT buffer on the net.

For example:

```
assign_local_clock -net localReset -type quadrant UR
```

Keep in mind the following when placing quadrant clocks using MultiView Navigator:

#### **Hardwired I/O–Driven CCCs**

- Find the associated clock input port under the Ports tab, and place the input port at one of the Gmn\* locations using PinEditor or I/O Attribute Editor, as shown in Figure 4-32.

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**Figure 4-32 • Port Assignment for a CCC with Hardwired I/O Clock Input**

## FlashROM Support in Flash-Based Devices

The flash FPGAs listed in Table 5-1 support the FlashROM feature and the functions described in this document.

**Table 5-1 • Flash-Based FPGAs**

Series	Family*	Description
IGLOO	IGLOO	Ultra-low power 1.2 V to 1.5 V FPGAs with Flash*Freeze technology
	IGLOOe	Higher density IGLOO FPGAs with six PLLs and additional I/O standards
	IGLOO nano	The industry's lowest-power, smallest-size solution
	IGLOO PLUS	IGLOO FPGAs with enhanced I/O capabilities
ProASIC3	ProASIC3	Low power, high-performance 1.5 V FPGAs
	ProASIC3E	Higher density ProASIC3 FPGAs with six PLLs and additional I/O standards
	ProASIC3 nano	Lowest-cost solution with enhanced I/O capabilities
	ProASIC3L	ProASIC3 FPGAs supporting 1.2 V to 1.5 V with Flash*Freeze technology
	RT ProASIC3	Radiation-tolerant RT3PE600L and RT3PE3000L
	Military ProASIC3/EL	Military temperature A3PE600L, A3P1000, and A3PE3000L
	Automotive ProASIC3	ProASIC3 FPGAs qualified for automotive applications
Fusion	Fusion	Mixed signal FPGA integrating ProASIC3 FPGA fabric, programmable analog block, support for ARM® Cortex™-M1 soft processors, and flash memory into a monolithic device

*Note:* \*The device names link to the appropriate datasheet, including product brief, DC and switching characteristics, and packaging information.

### **IGLOO Terminology**

In documentation, the terms IGLOO series and IGLOO devices refer to all of the IGLOO devices as listed in Table 5-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

### **ProASIC3 Terminology**

In documentation, the terms ProASIC3 series and ProASIC3 devices refer to all of the ProASIC3 devices as listed in Table 5-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

To further understand the differences between the IGLOO and ProASIC3 devices, refer to the *Industry's Lowest Power FPGAs Portfolio*.

## Simulation of FlashROM Design

The MEM file has 128 rows of 8 bits, each representing the contents of the FlashROM used for simulation. For example, the first row represents page 0, byte 0; the next row is page 0, byte 1; and so the pattern continues. Note that the three MSBs of the address define the page number, and the four LSBs define the byte number. So, if you send address 0000100 to FlashROM, this corresponds to the page 0 and byte 4 location, which is the fifth row in the MEM file. SmartGen defaults to 0s for any unspecified location of the FlashROM. Besides using the MEM file generated by SmartGen, you can create a binary file with 128 rows of 8 bits each and use this as a MEM file. Microsemi recommends that you use different file names if you plan to generate multiple MEM files. During simulation, Libero SoC passes the MEM file used as the generic file in the netlist, along with the design files and testbench. If you want to use different MEM files during simulation, you need to modify the generic file reference in the netlist.

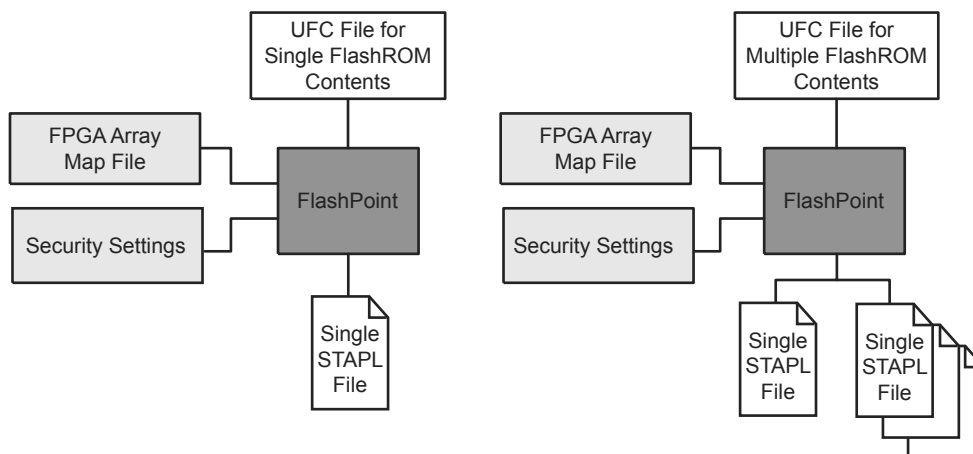
```
.....
UFROM0: UFROM
--generic map(MEMORYFILE => "F:\Appsnotes\FROM\test_designs\testa\smartgen\FROM_a.mem")
--generic map(MEMORYFILE => "F:\Appsnotes\FROM\test_designs\testa\smartgen\FROM_b.mem")
.....
```

The VITAL and Verilog simulation models accept the generics passed by the netlist, read the MEM file, and perform simulation with the data in the file.

## Programming File Generation for FlashROM Design

FlashPoint is the programming software used to generate the programming files for flash devices. Depending on the applications, you can use the FlashPoint software to generate a STAPL file with different FlashROM contents. In each case, optional AES decryption is available. To generate a STAPL file that contains the same FPGA core content and different FlashROM contents, the FlashPoint software needs an Array Map file for the core and UFC file(s) for the FlashROM. This final STAPL file represents the combination of the logic of the FPGA core and FlashROM content.

FlashPoint generates the STAPL files you can use to program the desired FlashROM page and/or FPGA core of the FPGA device contents. FlashPoint supports the encryption of the FlashROM content and/or FPGA Array configuration data. In the case of using the FlashROM for device serialization, a sequence of unique FlashROM contents will be generated. When generating a programming file with multiple unique FlashROM contents, you can specify in FlashPoint whether to include all FlashROM content in a single STAPL file or generate a different STAPL file for each FlashROM (Figure 5-11). The programming software (FlashPro) handles the single STAPL file that contains the FlashROM content from multiple devices. It enables you to program the FlashROM content into a series of devices sequentially (Figure 5-11). See the *FlashPro User's Guide* for information on serial programming.



**Figure 5-11 • Single or Multiple Programming File Generation**

- In Active and Static modes:
  - Input buffers with pull-up, driven Low
  - Input buffers with pull-down, driven High
  - Bidirectional buffers with pull-up, driven Low
  - Bidirectional buffers with pull-down, driven High
  - Output buffers with pull-up, driven Low
  - Output buffers with pull-down, driven High
  - Tristate buffers with pull-up, driven Low
  - Tristate buffers with pull-down, driven High
- In Flash\*Freeze mode:
  - Input buffers with pull-up, driven Low
  - Input buffers with pull-down, driven High
  - Bidirectional buffers with pull-up, driven Low
  - Bidirectional buffers with pull-down, driven High

## Electrostatic Discharge Protection

Low power flash devices are tested per JEDEC Standard JESD22-A114-B.

These devices contain clamp diodes at every I/O, global, and power pad. Clamp diodes protect all device pads against damage from ESD as well as from excessive voltage transients.

All IGLOO and ProASIC3 devices are tested to the Human Body Model (HBM) and the Charged Device Model (CDM).

Each I/O has two clamp diodes. One diode has its positive (P) side connected to the pad and its negative (N) side connected to VCCI. The second diode has its P side connected to GND and its N side connected to the pad. During operation, these diodes are normally biased in the off state, except when transient voltage is significantly above VCCI or below GND levels.

In 30K gate devices, the first diode is always off. In other devices, the clamp diode is always on and cannot be switched off.

By selecting the appropriate I/O configuration, the diode is turned on or off. Refer to Table 7-12 on page 193 for more information about the I/O standards and the clamp diode.

The second diode is always connected to the pad, regardless of the I/O configuration selected.

## Pro I/Os—IGLOOe, ProASIC3EL, and ProASIC3E

Table 8-2 shows the voltages and compatible I/O standards for Pro I/Os. I/Os provide programmable slew rates, drive strengths, and weak pull-up and pull-down circuits. All I/O standards, except 3.3 V PCI and 3.3 V PCI-X, are capable of hot-insertion. 3.3 V PCI and 3.3 V PCI-X can be configured to be 5 V-tolerant. See the "5 V Input Tolerance" section on page 232 for possible implementations of 5 V tolerance. Single-ended input buffers support both the Schmitt trigger and programmable delay options on a per-I/O basis.

All I/Os are in a known state during power-up, and any power-up sequence is allowed without current impact. Refer to the "I/O Power-Up and Supply Voltage Thresholds for Power-On Reset (Commercial and Industrial)" section in the datasheet for more information. During power-up, before reaching activation levels, the I/O input and output buffers are disabled while the weak pull-up is enabled. Activation levels are described in the datasheet.

**Table 8-2 • Supported I/O Standards**

	A3PE600	AGLE600	A3PE1500	A3PE3000/ A3PE3000L	AGLE3000
<b>Single-Ended</b>					
LVTTL/LVCMOS 3.3 V, LVCMOS 2.5 V / 1.8 V / 1.5 V, LVCMOS 2.5/5.0 V, 3.3 V PCI/PCI-X	✓	✓	✓	✓	✓
LVCMOS 1.2 V	–	✓	–	–	✓
<b>Differential</b>					
LVPECL, LVDS, B-LVDS, M-LVDS	✓	✓	✓	✓	✓
<b>Voltage-Referenced</b>					
GTL+ 2.5 V / 3.3 V, GTL 2.5 V / 3.3 V, HSTL Class I and II, SSTL2 Class I and II, SSTL3 Class I and II	✓	✓	✓	✓	✓

## **IGLOOe and ProASIC3E**

For devices requiring Level 3 and/or Level 4 compliance, the board drivers connected to the I/Os must have 10 k $\Omega$  (or lower) output drive resistance at hot insertion, and 1 k $\Omega$  (or lower) output drive resistance at hot removal. This resistance is the transmitter resistance sending a signal toward the I/O, and no additional resistance is needed on the board. If that cannot be assured, three levels of staging can be used to achieve Level 3 and/or Level 4 compliance. Cards with two levels of staging should have the following sequence:

- Grounds
- Powers, I/Os, and other pins

## **Cold-Sparing Support**

*Cold-sparing* refers to the ability of a device to leave system data undisturbed when the system is powered up, while the component itself is powered down, or when power supplies are floating.

Cold-sparing is supported on ProASIC3E devices only when the user provides resistors from each power supply to ground. The resistor value is calculated based on the decoupling capacitance on a given power supply. The RC constant should be greater than 3  $\mu$ s.

To remove resistor current during operation, it is suggested that the resistor be disconnected (e.g., with an NMOS switch) from the power supply after the supply has reached its final value. Refer to the "Power-Up/Down Behavior of Low Power Flash Devices" section on page 373 for details on cold-sparing.

Cold-sparing means that a subsystem with no power applied (usually a circuit board) is electrically connected to the system that is in operation. This means that all input buffers of the subsystem must present very high input impedance with no power applied so as not to disturb the operating portion of the system.

The 30 k gate devices fully support cold-sparing, since the I/O clamp diode is always off (see Table 8-13 on page 231). If the 30 k gate device is used in applications requiring cold-sparing, a discharge path from the power supply to ground should be provided. This can be done with a discharge resistor or a switched resistor. This is necessary because the 30 k gate devices do not have built-in I/O clamp diodes.

For other IGLOOe and ProASIC3E devices, since the I/O clamp diode is always active, cold-sparing can be accomplished either by employing a bus switch to isolate the device I/Os from the rest of the system or by driving each I/O pin to 0 V. If the resistor is chosen, the resistor value must be calculated based on decoupling capacitance on a given power supply on the board (this decoupling capacitance is in parallel with the resistor). The RC time constant should ensure full discharge of supplies before cold-sparing functionality is required. The resistor is necessary to ensure that the power pins are discharged to ground every time there is an interruption of power to the device.

IGLOOe and ProASIC3E devices support cold-sparing for all I/O configurations. Standards, such as PCI, that require I/O clamp diodes can also achieve cold-sparing compliance, since clamp diodes get disconnected internally when the supplies are at 0 V.

When targeting low power applications, I/O cold-sparing may add additional current if a pin is configured with either a pull-up or pull-down resistor and driven in the opposite direction. A small static current is induced on each I/O pin when the pin is driven to a voltage opposite to the weak pull resistor. The current is equal to the voltage drop across the input pin divided by the pull resistor. Refer to the "Detailed I/O DC Characteristics" section of the appropriate family datasheet for the specific pull resistor value for the corresponding I/O standard.

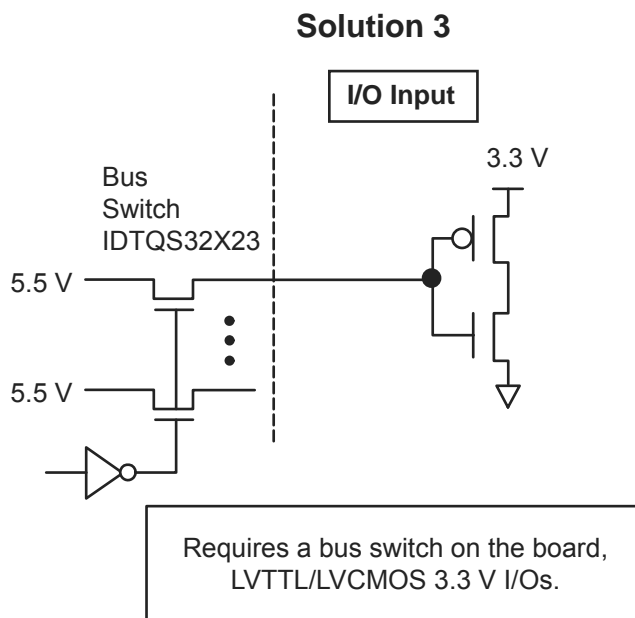
For example, assuming an LVTTTL 3.3 V input pin is configured with a weak pull-up resistor, a current will flow through the pull-up resistor if the input pin is driven LOW. For LVTTTL 3.3 V, the pull-up resistor is ~45 k $\Omega$ , and the resulting current is equal to  $3.3 \text{ V} / 45 \text{ k}\Omega = 73 \mu\text{A}$  for the I/O pin. This is true also when a weak pull-down is chosen and the input pin is driven High. This current can be avoided by driving the input Low when a weak pull-down resistor is used and driving it High when a weak pull-up resistor is used.



### Solution 3

The board-level design must ensure that the reflected waveform at the pad does not exceed the voltage overshoot/undershoot limits provided in the datasheet. This is a requirement to ensure long-term reliability.

This scheme will also work for a 3.3 V PCI/PCI-X configuration, but the internal diode should not be used for clamping, and the voltage must be limited by the bus switch, as shown in Figure 8-12. Relying on the diode clamping would create an excessive pad DC voltage of  $3.3\text{ V} + 0.7\text{ V} = 4\text{ V}$ .



**Figure 8-12 • Solution 3**

- Programming Centers

Microsemi programming hardware policy also applies to programming centers. Microsemi expects all programming centers to use certified programmers to program Microsemi devices. If a programming center uses noncertified programmers to program Microsemi devices, the "Noncertified Programmers" policy applies.

## Important Programming Guidelines

### Preprogramming Setup

Before programming, several steps are required to ensure an optimal programming yield.

#### ***Use Proper Handling and Electrostatic Discharge (ESD) Precautions***

Microsemi FPGAs are sensitive electronic devices that are susceptible to damage from ESD and other types of mishandling. For more information about ESD, refer to the *Quality and Reliability Guide*, beginning with page 41.

#### ***Use the Latest Version of the Designer Software to Generate Your Programming File (recommended)***

The files used to program Microsemi flash devices (\*.bit, \*.stp, \*.pdb) contain important information about the switches that will be programmed in the FPGA. Find the latest version and corresponding release notes at <http://www.microsemi.com/soc/download/software/designer/>. Also, programming files must always be zipped during file transfer to avoid the possibility of file corruption.

#### ***Use the Latest Version of the Programming Software***

The programming software is frequently updated to accommodate yield enhancements in FPGA manufacturing. These updates ensure maximum programming yield and minimum programming times. Before programming, always check the version of software being used to ensure it is the most recent. Depending on the programming software, refer to one of the following:

- FlashPro: [http://www.microsemi.com/soc/download/program\\_debug/flashpro/](http://www.microsemi.com/soc/download/program_debug/flashpro/)
- Silicon Sculptor: [http://www.microsemi.com/soc/download/program\\_debug/ss/](http://www.microsemi.com/soc/download/program_debug/ss/)

#### ***Use the Most Recent Adapter Module with Silicon Sculptor***

Occasionally, Microsemi makes modifications to the adapter modules to improve programming yields and programming times. To identify the latest version of each module before programming, visit [http://www.microsemi.com/soc/products/hardware/program\\_debug/ss/modules.aspx](http://www.microsemi.com/soc/products/hardware/program_debug/ss/modules.aspx).

#### ***Perform Routine Hardware Self-Diagnostic Test***

- Adapter modules must be regularly cleaned. Adapter modules need to be inserted carefully into the programmer to make sure the DIN connectors (pins at the back side) are not damaged.
- FlashPro

The self-test is only applicable when programming with FlashPro and FlashPro3 programmers. It is not supported with FlashPro4 or FlashPro Lite. To run the self-diagnostic test, follow the instructions given in the "Performing a Self-Test" section of [http://www.microsemi.com/soc/documents/FlashPro\\_UG.pdf](http://www.microsemi.com/soc/documents/FlashPro_UG.pdf).

- Silicon Sculptor

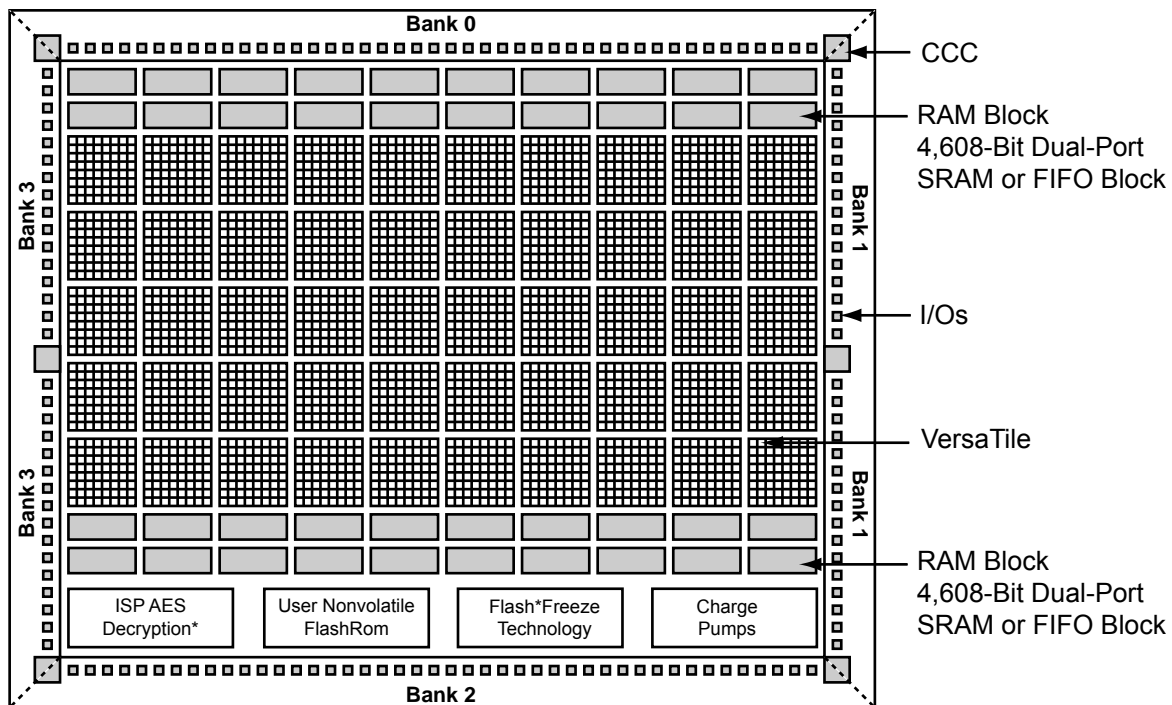
The self-diagnostic test verifies correct operation of the pin drivers, power supply, CPU, memory, and adapter module. This test should be performed with an adapter module installed and before every programming session. At minimum, the test must be executed every week. To perform self-diagnostic testing using the Silicon Sculptor software, perform the following steps, depending on the operating system:

- DOS: From anywhere in the software, type **ALT + D**.
- Windows: Click **Device** > choose **Actel Diagnostic** > select the **Test** tab > click **OK**.

Silicon Sculptor programmers must be verified annually for calibration. Refer to the *Silicon Sculptor Verification of Calibration Work Instruction* document on the website.

## Security Architecture

Fusion, IGLOO, and ProASIC3 devices have been designed with the most comprehensive programming logic design security in the industry. In the architecture of these devices, security has been designed into the very fabric. The flash cells are located beneath seven metal layers, and the use of many device design and layout techniques makes invasive attacks difficult. Since device layers cannot be removed without disturbing the charge on the programmed (or erased) flash gates, devices cannot be easily deconstructed to decode the design. Low power flash devices are unique in being reprogrammable and having inherent resistance to both invasive and noninvasive attacks on valuable IP. Secure, remote ISP is now possible with AES encryption capability for the programming file during electronic transfer. Figure 12-2 shows a view of the AES decryption core inside an IGLOO device; Figure 12-3 on page 304 shows the AES decryption core inside a Fusion device. The AES core is used to decrypt the encrypted programming file when programming.



Note: \*ISP AES Decryption is not supported by 30 k gate devices and smaller. For details of other architecture features by device, refer to the appropriate family datasheet.

**Figure 12-2 • Block Representation of the AES Decryption Core in IGLOO and ProASIC3 Devices**

The AES key is securely stored on-chip in dedicated low power flash device flash memory and cannot be read out. In the first step, the AES key is generated and programmed into the device (for example, at a secure or trusted programming site). The Microsemi Designer software tool provides AES key generation capability. After the key has been programmed into the device, the device will only correctly decrypt programming files that have been encrypted with the same key. If the individual programming file content is incorrect, a Message Authentication Control (MAC) mechanism inside the device will fail in authenticating the programming file. In other words, when an encrypted programming file is being loaded into a device that has a different programmed AES key, the MAC will prevent this incorrect data from being loaded, preventing possible device damage. See Figure 12-3 on page 304 and Figure 12-4 on page 306 for graphical representations of this process.

It is important to note that the user decides what level of protection will be implemented for the device. When AES protection is desired, the FlashLock Pass Key must be set. The AES key is a content protection mechanism, whereas the FlashLock Pass Key is a device protection mechanism. When the AES key is programmed into the device, the device still needs the Pass Key to protect the FPGA and FlashROM contents and the security settings, including the AES key. Using the FlashLock Pass Key prevents modification of the design contents by means of simply programming the device with a different AES key.

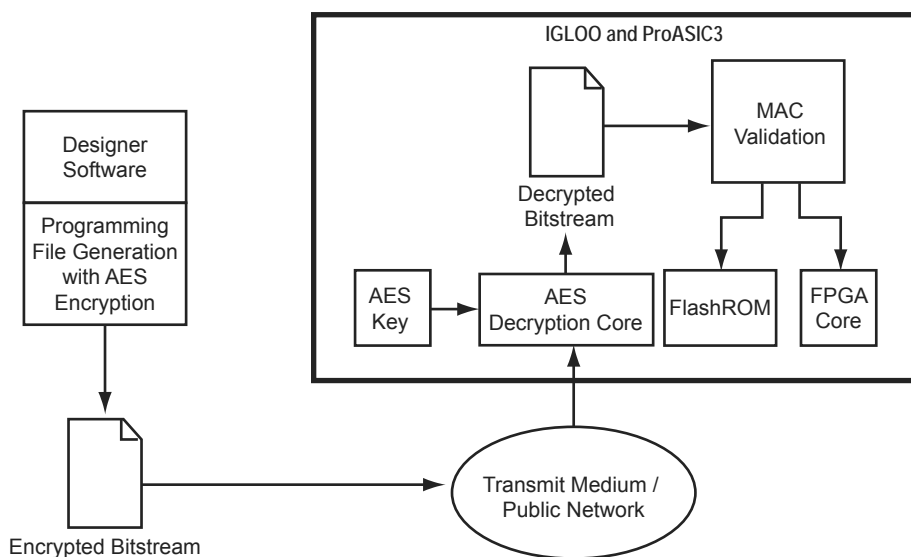
### **AES Decryption and MAC Authentication**

Low power flash devices have a built-in 128-bit AES decryption core, which decrypts the encrypted programming file and performs a MAC check that authenticates the file prior to programming.

MAC authenticates the entire programming data stream. After AES decryption, the MAC checks the data to make sure it is valid programming data for the device. This can be done while the device is still operating. If the MAC validates the file, the device will be erased and programmed. If the MAC fails to validate, then the device will continue to operate uninterrupted.

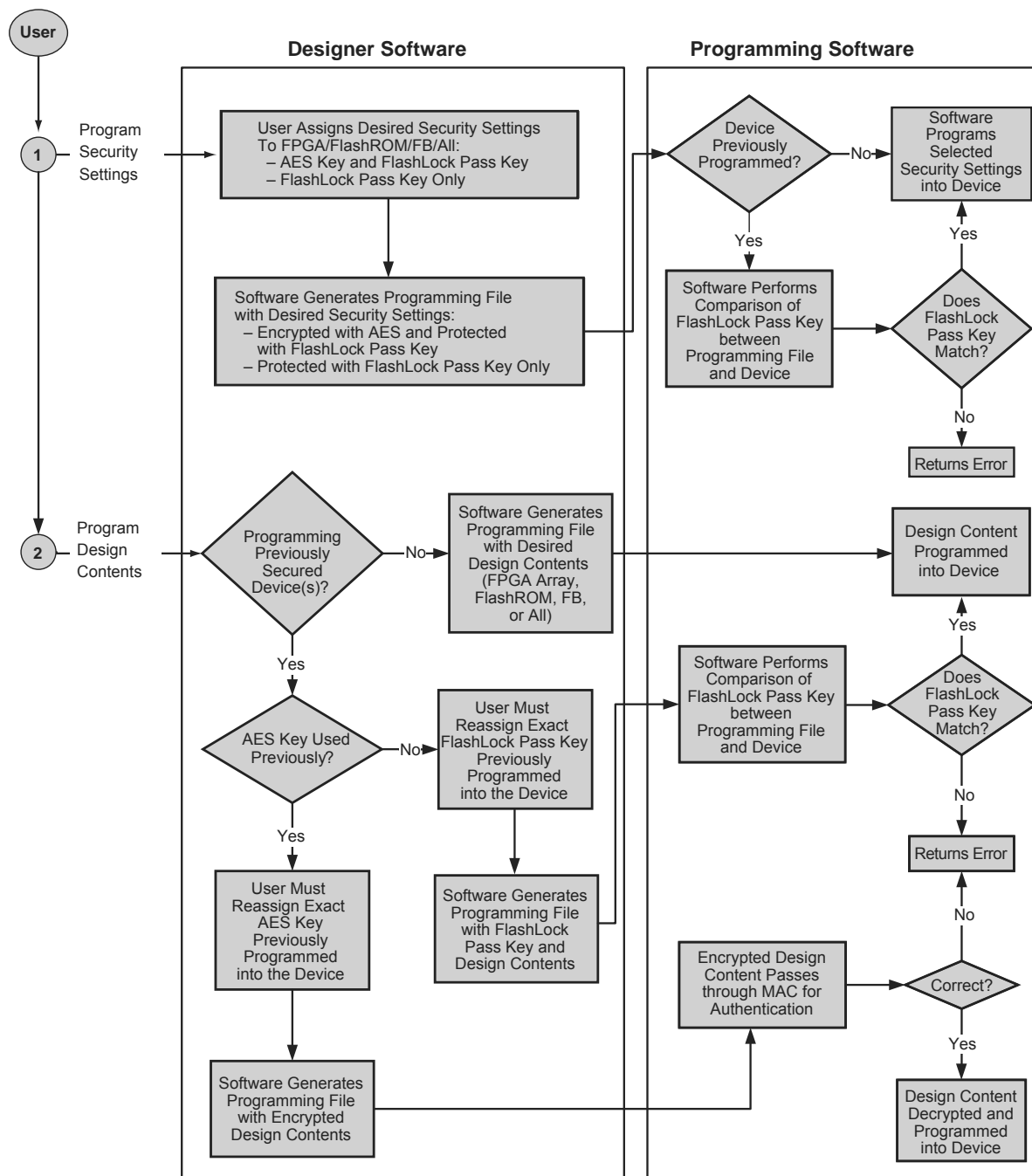
This will ensure the following:

- Correct decryption of the encrypted programming file
- Prevention of erroneous or corrupted data being programmed during the programming file transfer
- Correct bitstream passed to the device for decryption



**Figure 12-4 • Example Application Scenario Using AES in IGLOO and ProASIC3 Devices**

1. National Institute of Standards and Technology, "ADVANCED ENCRYPTION STANDARD (AES) Questions and Answers," 28 January 2002 (10 January 2005). See <http://csrc.nist.gov/archive/aes/index1.html> for more information.



*Note: If programming the Security Header only, just perform sub-flow 1.  
If programming design content only, just perform sub-flow 2.*

**Figure 12-9 • Security Programming Flows**

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**Figure 12-19 • FlashLock Pass Key, Previously Programmed Devices**

It is important to note that when the security settings need to be updated, the user also needs to select the **Security settings** check box in Step 1, as shown in Figure 12-10 on page 314 and Figure 12-11 on page 314, to modify the security settings. The user must consider the following:

- If only a new AES key is necessary, the user must re-enter the same Pass Key previously programmed into the device in Designer and then generate a programming file with the same Pass Key and a different AES key. This ensures the programming file can be used to access and program the device and the new AES key.
- If a new Pass Key is necessary, the user can generate a new programming file with a new Pass Key (with the same or a new AES key if desired). However, for programming, the user must first load the original programming file with the Pass Key that was previously used to unlock the device. Then the new programming file can be used to program the new security settings.

## Advanced Options

As mentioned, there may be applications where more complicated security settings are required. The “Custom Security Levels” section in the *FlashPro User's Guide* describes different advanced options available to aid the user in obtaining the best available security settings.

## 16 – Boundary Scan in Low Power Flash Devices

### Boundary Scan

Low power flash devices are compatible with IEEE Standard 1149.1, which defines a hardware architecture and the set of mechanisms for boundary scan testing. JTAG operations are used during boundary scan testing.

The basic boundary scan logic circuit is composed of the TAP controller, test data registers, and instruction register (Figure 16-2 on page 360).

Low power flash devices support three types of test data registers: bypass, device identification, and boundary scan. The bypass register is selected when no other register needs to be accessed in a device. This speeds up test data transfer to other devices in a test data path. The 32-bit device identification register is a shift register with four fields (LSB, ID number, part number, and version). The boundary scan register observes and controls the state of each I/O pin. Each I/O cell has three boundary scan register cells, each with serial-in, serial-out, parallel-in, and parallel-out pins.

### TAP Controller State Machine

The TAP controller is a 4-bit state machine (16 states) that operates as shown in Figure 16-1.

The 1s and 0s represent the values that must be present on TMS at a rising edge of TCK for the given state transition to occur. IR and DR indicate that the instruction register or the data register is operating in that state.

The TAP controller receives two control inputs (TMS and TCK) and generates control and clock signals for the rest of the test logic architecture. On power-up, the TAP controller enters the Test-Logic-Reset state. To guarantee a reset of the controller from any of the possible states, TMS must remain HIGH for five TCK cycles. The TRST pin can also be used to asynchronously place the TAP controller in the Test-Logic-Reset state.

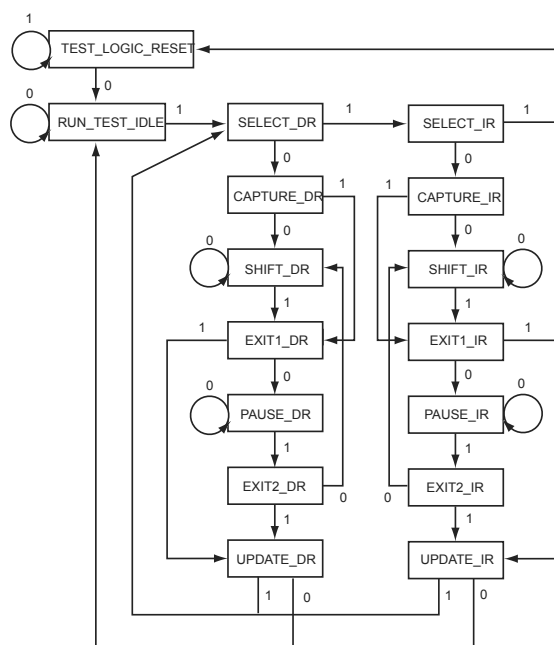


Figure 16-1 • TAP Controller State Machine

## Conclusion

Microsemi low power flash FPGAs offer many unique advantages, such as security, nonvolatility, reprogrammability, and low power—all in a single chip. In addition, Fusion, IGLOO, and ProASIC3 devices provide access to the JTAG port from core VersaTiles while the device is in normal operating mode. A wide range of available user-defined JTAG opcodes allows users to implement various types of applications, exploiting this feature of these devices. The connection between the JTAG port and core tiles is implemented through an embedded and hardwired UJTAG tile. A UJTAG tile can be instantiated in designs using the UJTAG library cell. This document presents multiple examples of UJTAG applications, such as dynamic reconfiguration, silicon test and debug, fine-tuning of the design, and RAM initialization. Each of these applications offers many useful advantages.

## Related Documents

### Application Notes

*RAM Initialization and ROM Emulation in ProASIC<sup>PLUS</sup> Devices*  
[http://www.microsemi.com/soc/documents/APA\\_RAM\\_Initd\\_AN.pdf](http://www.microsemi.com/soc/documents/APA_RAM_Initd_AN.pdf)

## List of Changes

The following table lists critical changes that were made in each revision of the chapter.

Date	Changes	Page
December 2011	Information on the drive strength and slew rate of TDO pins was added to the "Silicon Testing and Debugging" section (SAR 31749).	370
July 2010	This chapter is no longer published separately with its own part number and version but is now part of several FPGA fabric user's guides.	N/A
v1.4 (December 2008)	IGLOO nano and ProASIC3 nano devices were added to Table 17-1 • Flash-Based FPGAs.	364
v1.3 (October 2008)	The "UJTAG Support in Flash-Based Devices" section was revised to include new families and make the information more concise.	364
	The title of Table 17-3 • Configuration Bits of Fusion, IGLOO, and ProASIC3 CCC Blocks was revised to include Fusion.	368
v1.2 (June 2008)	The following changes were made to the family descriptions in Table 17-1 • Flash-Based FPGAs: <ul style="list-style-type: none"> <li>ProASIC3L was updated to include 1.5 V.</li> <li>The number of PLLs for ProASIC3E was changed from five to six.</li> </ul>	364
v1.1 (March 2008)	The chapter was updated to include the IGLOO PLUS family and information regarding 15 k gate devices.	N/A
	The "IGLOO Terminology" section and "ProASIC3 Terminology" section are new.	364



Revision (month/year)	Chapter Affected	List of Changes (page number)
Revision 0 (continued)	"DDR for Microsemi's Low Power Flash Devices" was revised.	285
	"Programming Flash Devices" was revised.	298
	"In-System Programming (ISP) of Microsemi's Low Power Flash Devices Using FlashPro4/3/3X" was revised.	339
	"Core Voltage Switching Circuit for IGLOO and ProASIC3L In-System Programming" was revised.	347
	"Boundary Scan in Low Power Flash Devices" was revised.	362